

## Schottky Diode Type 3DSF10

### Product Description

Type 3DSFx family of structures are fabricated by ACST Film-Diode (FD) Process. FD-Structures are implemented on a transferred membrane-Substrate, which is just few  $\mu\text{m}$  thin and of a low dielectric constant insulator. This allows for a drastic reduction of structure parasitic and, therefore, aims at ultimate performance at MM/SubMM-Waves. Optically-transparent membrane-substrate allows for accurate positioning for diode mounting/assembly.

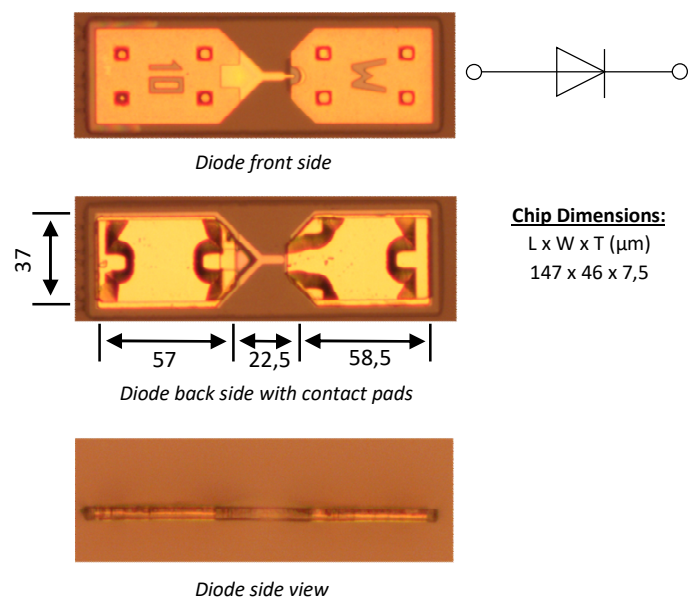


Fig. 1: Optical view of the product

The 3DSF structure represents a single-anode Schottky diode, optimised for operation in varistor mode under Zero-Bias Condition. Low differential resistance enables easy matching with 50\_Ohm reading electronics, which is of a crucial importance for high-speed electronics (data transmission systems).

### Application Areas

- Zero-Bias square-law (envelope) detectors
- Power sensors
- Frequency mixers with low-LO-requirements
- High-frequency low-power rectifiers for wireless power transmission

### Product features

- Low noise due to 0V-bias
- Low 0V differential resistance (easy matching with 50\_Ohm reading electronics)
- Strongly reduced shunt (pad-to-pad) capacitance
- Suitable for flip-chip mounting approach
- Structure geometry optimized for MM/SubMM-Waves applications

## Application Note

- This diode can be assembled onto RF-circuit-substrate by soldering or by gluing contact pads using a conductive adhesive. Maximal temperature for soldering is 170 °C for a duration of maximum 30 sec.  
Curing temperature of conductive adhesive should not exceed 125 °C for a duration of maximum 30 min. Higher curing temperature and/or longer curing time can lead to increase of differential resistance  $R_d$  of the diode and in extreme cases can cause total device failure.
- Contact pads are finished by a 500nm Gold layer and are situated on the **back-side** of the diode structure. For user reference: contact pads do not have individual markers like "W17". Individual markers are seen only on the front-side of the structure.
- Front-side of the structure is covered by a transparent insulator film (Film-Substrate) and is not suited for assembly. However, the Film-Substrate has windows, which allow contacting (whiskering) the diode from front-side for electrical measurements even after diode has been mounted/soldered/glued onto RF-circuit substrate.

Tab. 1: Electrical parameters at room temperature

Parameter	Symbol	Specified Range		
		Minimum	Nom.	Maximum
Chip length [ $\mu\text{m}$ ]	L	146	147	157
Chip width [ $\mu\text{m}$ ]	W	45	46	56
Chip thickness [ $\mu\text{m}$ ]	T	6.5	7.5	8.5
Total capacitance [fF]	$C_{\text{tot}}$	10.5	13	15.5
Junction capacitance [fF]	$C_{j0}$	8	10	12
Forward voltage at current level of 100 $\mu\text{A}$ [mV]	$V_{f@100\mu\text{A}}$	40	46	52
*Junction Resistance at 0V [ $\Omega$ ]	$R_{\text{dif}}$	800	1000	1200
**Current Responsivity at 0V [A/W]	$\beta_0$	14.6	14.7	14.8

## Comments

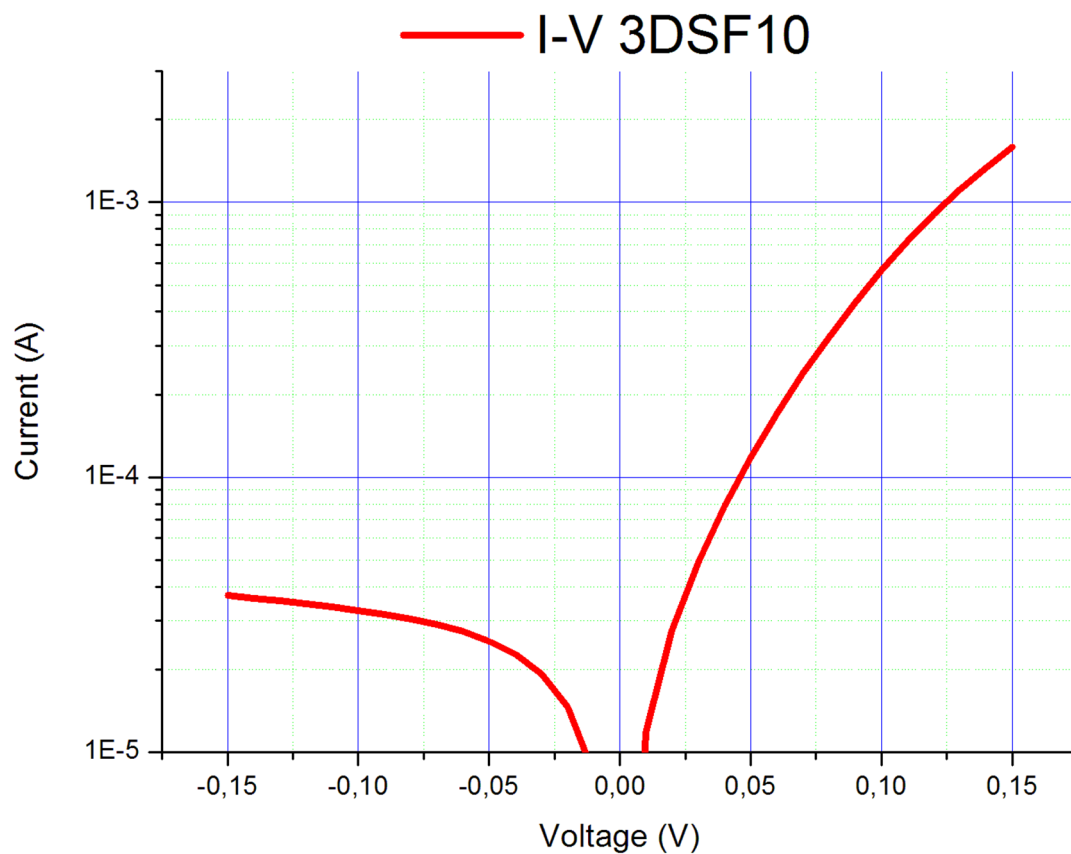
\*  $R_J$  - Junction Resistance (0V):

$$R_J = \frac{1}{\frac{dI}{dV}} = \frac{dV}{dI}$$

\*\*  $\beta_0$  - Current Responsivity (0V):

$$\beta_0 = -\frac{\frac{d^2V}{dI^2}}{2 \cdot \left(\frac{dV}{dI}\right)^2}$$

## Typical Forward IV Curve (22 °C)



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